

<b>INFORMATION DISCLOSURE STATEMENT</b>  <b>PTO-1449</b>	Atty. Docket No. <b>031171</b>	Serial No. <b>New Application</b>
	Applicant(s): <b>Hiroji EBE, et al.</b>	
	Filing Date: <b>September 16, 2003</b>	Group Art Unit: <b>Not Yet Assigned</b>

#### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					
_____	AC					
_____	AD					

#### FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)
<i>DP</i>	AE 9-326506	12/16/97	Japan	Yes-Abstract/Discussed in the specification
	AF			

#### OTHER DOCUMENTS

<i>PF</i>	AG	D. Leonard et al.; "Direct formation of quantum-sized dots from uniform coherent islands of InGaAs on GaAs surfaces"; <i>Applied Physics Letters</i> ; Vol. 63; No. 23; December 6 1993; pp. 3203-3205./Discussed in the specification.
<i>DE</i>	AH	K. Mukai et al.; "Self-Formed $In_{0.5}Ga_{0.5}As$ Quantum Dots on GaAs Substrates Emitting at $1.3\mu m$ "; <i>Japanese Journal of Applied Physics</i> ; Vol. 33; Part 2, No. 12A; December 1 1994; pp. L1710-1712./Discussed in the specification.
<i>PF</i>	AI	J. Oshinowo et al.; "Highly uniform InGaAs/GaAs quantum dots (~15 nm) by metalorganic chemical vapor deposition"; <i>Applied Physics Letters</i> ; Vol. 65; No. 11; September 12 1994; pp. 1421-1423./Discussed in the specification.

Examiner	<i>Dan J. S.</i>	Date Considered	<i>5/11/05</i>
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